



安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

RS1A THRU RS1M

1.0 AMP SURFACE MOUNT FAST RECOVERY RECTIFIERS



FEATURES

- * Ideal for surface mount applications
- * Easy pick and place
- * Built-in strain relief
- * Fast switching speed

MECHANICAL DATA

- * Case: Molded plastic
- * Epoxy: UL 94V-0 rate flame retardant
- * Metallurgically bonded construction
- * Polarity: Color band denotes cathode end
- * Mounting position: Any
- * Weight: 0.063 grams

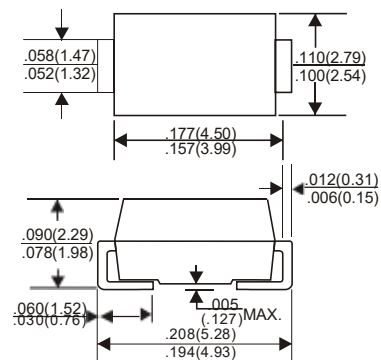
VOLTAGE RANGE

50 to 1000 Volts

CURRENT

1.0 Ampere

DO-214AC(SMA)



Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating 25 °C ambient temperature unless otherwise specified.

Single phase half wave, 60Hz, resistive or inductive load.

For capacitive load, derate current by 20%.

TYPE NUMBER	RS1A	RS1B	RS1D	RS1G	RS1J	RS1K	RS1M	UNITS
Maximum Recurrent Peak Reverse Voltage	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current .375"(9.5mm) Lead Length at Ta=55 C	1.0							A
Peak Forward Surge Current, 8.3 ms single half sine-wave superimposed on rated load (JEDEC method)	30							A
Maximum Instantaneous Forward Voltage at 1.0A	1.3							V
Maximum DC Reverse Current Ta=25 C	5.0							A
at Rated DC Blocking Voltage Ta=100°C	100							A
Maximum Reverse Recovery Time (Note 1)	150			250		500		nS
Typical Junction Capacitance (Note 2)	15							pF
Operating and Storage Temperature Range T _J , T _{STG}	-65—+150							°C

NOTES:

1. Reverse Recovery Time test condition: IF=0.5A, IR=1.0A, IRR=0.25A

2. Measured at 1MHz and applied reverse voltage of 4.0V D.C.

RATING AND CHARACTERISTIC CURVES (RS1A THRU RS1M)

FIG.1-TYPICAL FORWARD CHARACTERISTICS

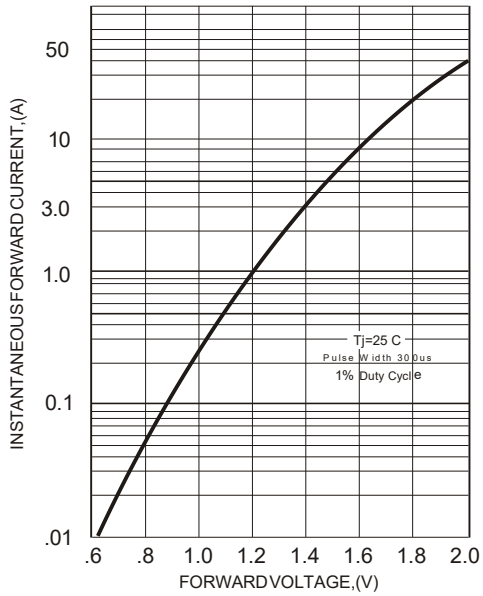


FIG.2-TYPICAL FORWARD CURRENT DERATING CURVE

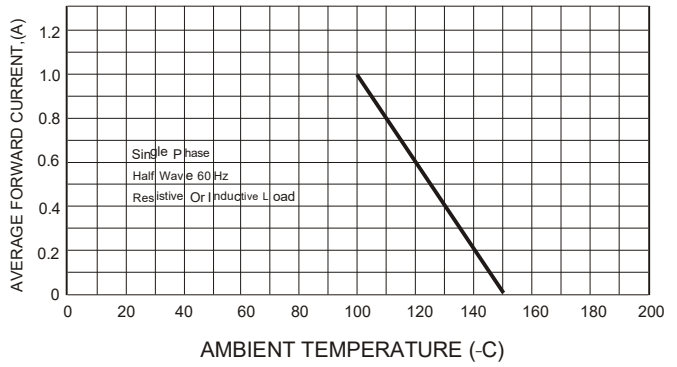
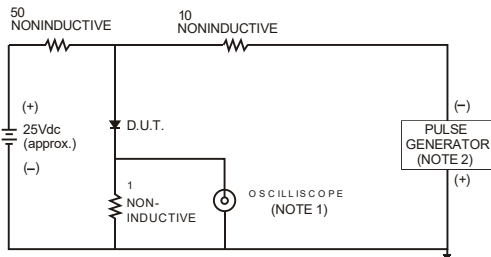


FIG.3- TEST CIRCUIT DIAGRAM AND REVERSE RECOVERY TIME CHARACTERISTICS



- NOTES: 1. Rise Time= 7ns max., Input Impedance= 1 megohm.22pF.
 2. Rise Time= 10ns max., Source Impedance= 50 ohms.

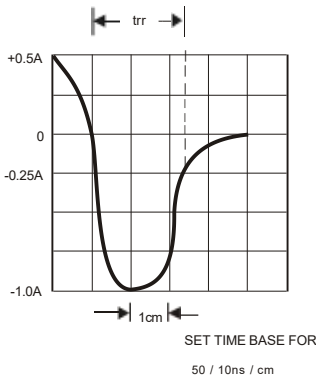


FIG.4-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

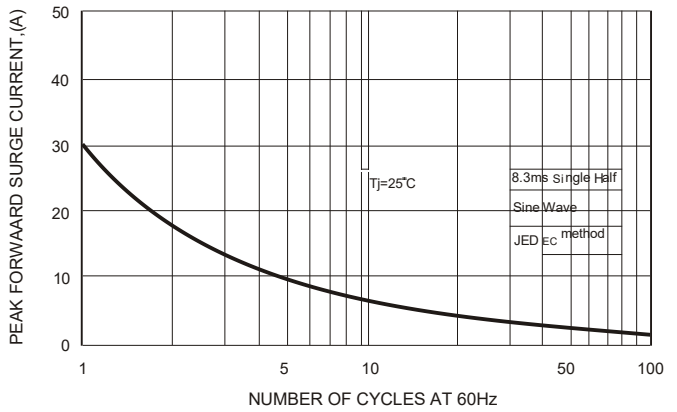


FIG.5-TYPICAL JUNCTION CAPACITANCE

